selected from the group consisting of Y, Sc and La, and 2) at least one element selected from the group consisting of Al and Ga and being activated with cerium.--

--35. A light emitting device according to claim 34, wherein said gallium nitride based compound semiconductor is a gallium nitride semiconductor containing In.--

--36. A light emitting device according to claim 34, wherein said gallium nitride based compound semiconductor is represented by the formula: $Ga_xAl_{1-x}N$ or $Ga_xIn_{1-x}N$.-

--37. A light emitting device according to claim 34, wherein the phosphor used contains an yttrium-aluminum-garnet fluorescent material containing Y and Al.--

--38. A light emitting device according to claim 34, wherein the main emission peak of the light emitting component is set within the range from 420 nm to 460 nm and the main emission wavelength of the phosphor is set to be longer then the main emission peak of the light emitting component.--

--39. A light emitting device according to claim 38, wherein the light emitting layer of the light emitting component contains a gallium nitride semiconductor containing In, and the phosphor is an yttrium-aluminum-garnet fluorescent material.--

--40. An LED display device comprising the light emitting device according to claim 34 arranged in a matrix and a drive circuit which drives the LED display device according to display data which is input thereto.—

--41. A full-color LED display device comprising the light emitting device according to claim 34.--

--42. A light emitting diode comprising:

a mount lead having a cup and a lead;

an LED chip mounted in the cup of the mount lead with one of electrodes being electrically connected to the mount lead;

a transparent coating material filling the cup to cover the LED chip; and

a light emitting diode having a molding material which covers the LED chip covered with the coating material including the cup of the mount lead, the inner lead and another electrode of the LED chip, wherein

the LED chip is a nitride compound semiconductor and the coating material contains at least one element selected from the group consisting of Y, Sc and La, at least one element selected from the group consisting of Al, Ga and In.—

--43. A light emitting diode according to claim 42, wherein said nitride compound semiconductor is a gallium nitride based compound semiconductor.--

--44. A light emitting diode according to claim 43, wherein said gallium nitride based compound semiconductor is a gallium nitride semiconductor containing In.--

--45. A light emitting diode according to claim 43, wherein said gallium nitride based compound semiconductor is represented by the formula: $Ga_xAl_{1-x}N$ or $Ga_xIn_{1-x}N$.-

--46. A light emitting diode according to claim 42, wherein the phosphor used contains an yttrium-aluminum-garnet fluorescent material that contains Y and Al.--

--47. A light emitting diode according to claim 42, wherein the main emission peak of the light emitting component is set within the range of 420 nm to 460 nm and the main emission wavelength of the phosphor is set to be longer than the main emission peak of the light emitting component.--

--48. A white light emitting diode comprising a light emitting component using a semiconductor as a light emitting layer and a phosphor which absorbs a part of the light emitted by the light emitting component and emits light of wavelength different from that of the absorbed light, wherein the light emitting layer of the light emitting component is a nitride compound semiconductor and the phosphor contains garnet fluorescent material activated with cerium which contains at least one element selected from the group consisting of Y, Sc and La, and at least one element selected from the group consisting of Al and Ga, and wherein the main emission peak of the light emitting component is set within the range from 420 nm to 460 nm and the main emission wavelength of the phosphor is set to be longer than the main emission peak of the light emitting component.

--49. A light emitting diode according to claim 42, wherein said nitride compound semiconductor is a gallium nitride based compound semiconductor.--

--50. A light emitting diode according to claim 43, wherein said gallium nitride based compound semiconductor is a gallium nitride semiconductor containing In.--

--51. A light emitting diode according to claim 43, wherein said gallium nitride based compound semiconductor is represented by the formula: $Ga_xAl_{1-x}N$ or $Ga_xIn_{1-x}N$.-

REMARKS